

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,018,908 B2
APPLICATION NO. : 10/815065
DATED : March 28, 2006
INVENTOR(S) : Sujit Sharan

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Col. 5, line 27 –

Replace “silicon dioxide leyer is comprised by a shallow trench”

Insert --silicon dioxide layer is comprised by a shallow trench--

Col. 5, line 56 –

Replace “forming era opening extending into a substrate;”

Insert --forming an opening extending into a substrate;--

Col. 6, line 35 –

Replace “contacts the fleet layer”

Insert --contacts the first layer--

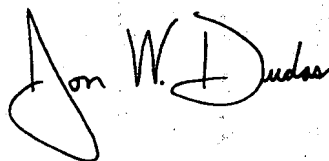
Col. 7, line 4 –

Replace “layers within the opening end the forming of the second”

Insert --layers within the opening and the forming of the second--

Signed and Sealed this

Twenty-third Day of October, 2007

A handwritten signature in black ink, appearing to read "Jon W. Dudas". The signature is stylized with a large, looped initial "J" and a distinct "D".

JON W. DUDAS

Director of the United States Patent and Trademark Office